



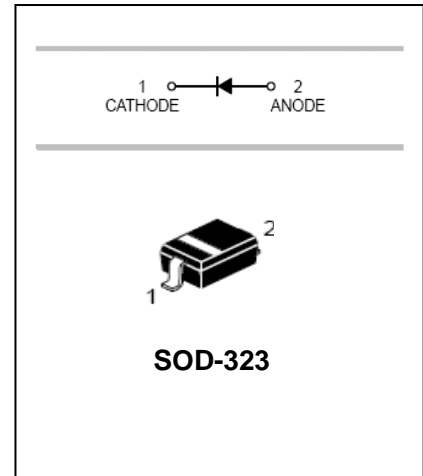
## Silicon Epitaxial Planar Diode **BAV19WS/BAV20WS/BAV21WS**

### FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance



Lead-free



### APPLICATIONS

- Surface mount fast switching diode

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| BAV19WS  | A8      | SOD-323      |
| BAV20WS  | T2      | SOD-323      |
| BAV21WS  | T3      | SOD-323      |

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

| Characteristic                             | Symbol          | BAV19WS     | BAV20WS | BAV21WS | Unit |
|--|-----------------|-------------|---------|---------|------|
| Repetitive Peak Reverse Voltage            | $V_{RRM}$       | 120         | 200     | 250     | V    |
| Working Peak Reverse Voltage               | $V_{RWM}$       | 100         | 150     | 200     | V    |
| DC Reverse Voltage                         | $V_R$           |             |         |         | V    |
| RMS Reverse Voltage                        | $V_{R(RMS)}$    | 71          | 106     | 141     | V    |
| Average Rectified Output Current           | $I_o$           | 200         |         |         | mA   |
| Non-Repetitive Peak Forward Surge Current  | $I_{FSM}$       | 2.5         |         |         | A    |
| @t=1.0 $\mu$ s                             |                 |             |         |         |      |
| @t=1.0 s                                   |                 | 0.5         |         |         |      |
| Repetitive Peak Forward Surge Current      | $I_{FRM}$       | 625         |         |         | mA   |
| Power Dissipation                          | $P_d$           | 200         |         |         | mW   |
| Thermal Resistance Junction to Ambient Air | $R_{\theta JA}$ | 625         |         |         | °C/W |
| Operating and Storage Temperature Range    | $T_j, T_{STG}$  | -65 to +150 |         |         | °C   |



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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| Characteristic   | Symbol      | Min               | Max               | Unit    | Test Condition  |
|--|-------------|-------------------|-------------------|---------|---|
| Reverse Breakdown Voltage<br>BAV19WS<br>BAV20WS<br>BAV21WS | $V_{(BR)R}$ | 120<br>200<br>250 |                   | V       | $I_R=100\mu A$  |
| Forward Voltage  | $V_{FM}$    | -                 | 1.0<br>1.25       | V       | $I_F=100mA$<br>$I_F=200mA$                                |
| Reverse Current BAV19WS<br>BAV20WS<br>BAV21WS              | $I_R$       | -                 | 0.1<br>0.1<br>0.1 | $\mu A$ | $V_R=100V$<br>$V_R=150V$<br>$V_R=200V$                    |
| Capacitance between terminals                              | $C_T$       | -                 | 5                 | pF      | $V_R=0, f=1.0MHz$   |
| Reverse Recovery Time                                      | $t_{rr}$    | -                 | 50                | ns      | $I_F=I_R=30mA,$<br>$I_{rr}=0.1 \times I_R, R_L=100\Omega$ |

**Silicon Epitaxial Planar Diode BAV19WS/BAV20WS/BAV21WS**

TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

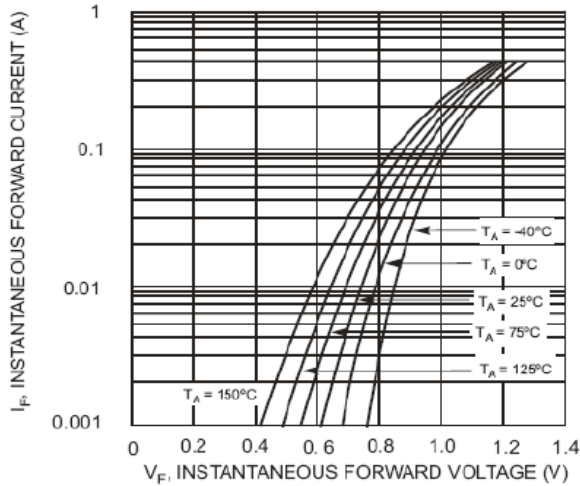


Fig. 1 Typical Forward Characteristics

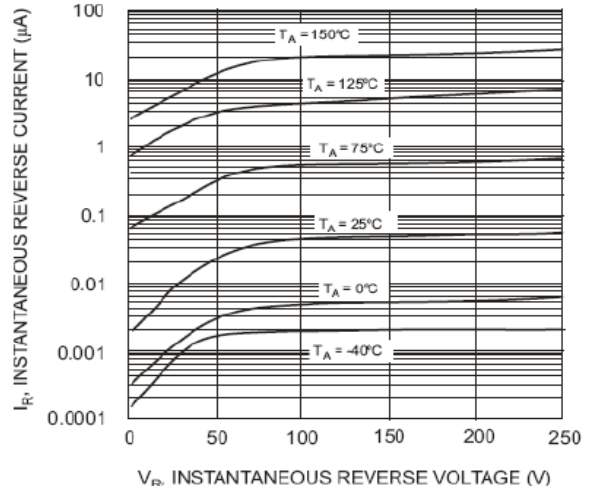


Fig. 2 Typical Reverse Characteristics

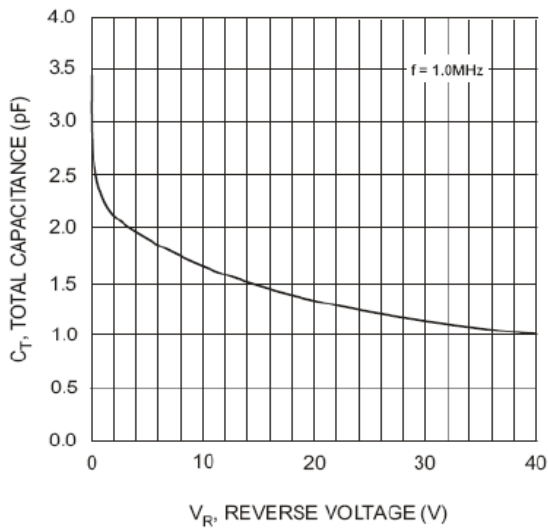


Fig. 3 Typical Capacitance vs. Reverse Voltage

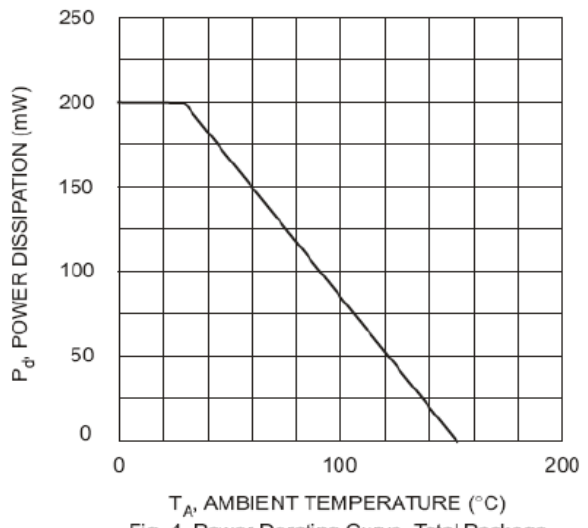


Fig. 4 Power Derating Curve, Total Package

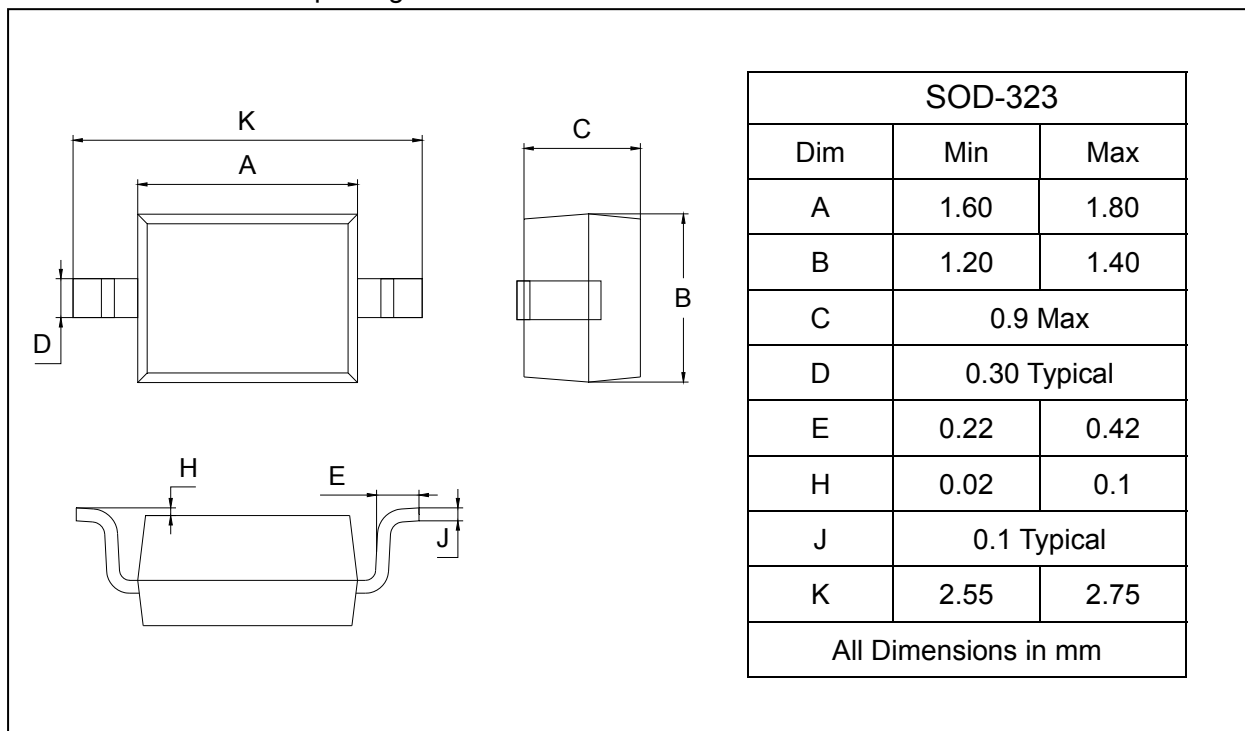


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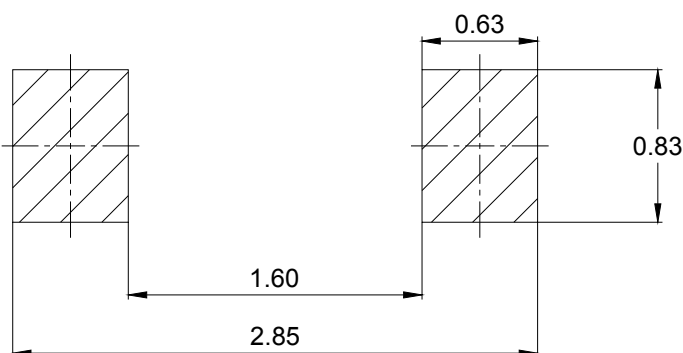
**PACKAGE OUTLINE**

Plastic surface mounted package

SOD-323



**SOLDERING FOOTPRINT**



Unit : mm

**PACKAGE INFORMATION**

| Device            | Package | Shipping       |
|-------------------|---------|----------------|
| BAV19WS/20WS/21WS | SOD-323 | 3000/Tape&Reel |